

ABSTRACT

The present invention relates to a photo-detecting device having a structure which enables an increase of the number of pixels and advanced high density and further enables precise photo-detection. The photo-detecting device includes N photodiodes, N switches, a common wire, an integrating circuit, a first substrate provided with the N photodiodes, and a second substrate provided with the N switches, common wire, and integrating circuit. The N photodiodes and N switches to be electrically connected to each other are electrically connected by bump-connecting the first substrate and the second substrate. In such a construction, a connection wire two-dimensionally laid out that electrically connects the N photodiodes and N switches is unnecessary, thereby shortening the wire path length (reduction of noise). In addition, when the first substrate provided with the N photodiodes are bump-connected to the second substrate provided with the remaining electronic devices, which enables integration of the photodiodes without any consideration for wire layout on the first substrate (high density of pixels).